L Number	Hits	Search Text	DB	Time stamp
1	1	("6362035").PN.	USPAT; US-PGPUB; IBM_TDB	2004/09/13 13:26
2	0	("200400132263").PN.	USPAT; US-PGPUB; IBM_TDB	2004/09/13 13:27
3	1	("20040132263").PN.	USPAT; US-PGPUB; IBM_TDB	2004/09/13 13:27
-	14	lee-jae-kyu.in.	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:53
-	1703	(438/424,433,435,437).CCLS.	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:53
-	1414	((438/424,433,435,437).CCLS.) and @ad<20020724 not samsung.as.	USPAT; US-PGPUB; IBM_TDB	2004/09/13 10:34
-	11692	sti "shallow trench isolation"	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:53
-	14962	"trench isolation" (sti "shallow trench isolation")	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:54
-	76730	well with (resistance shallow)	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:54
-	13658	well near low	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:54
-	2096	(well with (resistance shallow)) and (well near low)	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:54
-	41	((well with (resistance shallow)) and (well near low)) and ("trench isolation" (sti "shallow trench isolation"))	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:54
-	34	(((well with (resistance shallow)) and (well near low)) and ("trench isolation" (sti "shallow trench isolation"))) and @ad<20020724 not samsung.as.	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:56
-	44963	ion with implantation	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:57
-	400	(ion with implantation) and (((438/424,433,435,437).CCLS.) and @ad<20020724 not samsung.as.)	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:57
-	5449	(ion with implantation) and ("trench isolation" (sti "shallow trench isolation"))	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:57
-	45909	low near (energy dose)	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:57

-	3771	(low near (energy dose)) and (ion with implantation)	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:57
-	548	((low near (energy dose)) and (ion with implantation)) and ("trench isolation" (sti "shallow trench isolation"))	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:57
-	496	(((low near (energy dose)) and (ion with implantation)) and ("trench isolation" (sti "shallow trench isolation"))) and well	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:58
-	356	((((low near (energy dose)) and (ion with implantation)) and ("trench isolation" (sti "shallow trench isolation"))) and well) and @ad<20020724 not samsung.as.	USPAT; US-PGPUB; IBM_TDB	2004/09/10 14:31
-	351	(((((low near (energy dose)) and (ion with implantation)) and ("trench isolation" (sti "shallow trench isolation"))) and well) and @ad<20020724 not samsung.as.) and (438/$3 257/$3).ccls.	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:58
-	5449	((ion with implantation) and ("trench isolation" (sti "shallow trench isolation"))) ((((((low near (energy dose)) and (ion with implantation)) and ("trench isolation" (sti "shallow trench isolation"))) and well) and @ad<20020724 not samsung.as.) and (438/$3 257/$3).ccls.)	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:58
-	731	((ion with implantation) and (((438/424,433,435,437).CCLS.) and @ad<20020724 not samsung.as.)) ((((((low near (energy dose)) and (ion with implantation)) and ("trench isolation" (sti "shallow trench isolation"))) and well) and @ad<20020724 not samsung.as.) and (438/$3 257/$3).ccls.)	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:58
-	4557	nitride and (((ion with implantation) and ("trench isolation" (sti "shallow trench isolation"))) ((((((low near (energy dose)) and (ion with implantation)) and ("trench isolation" (sti "shallow trench isolation"))) and well) and @ad<20020724 not samsung.as.) and (438/$3 257/$3).ccls.))	USPAT; US-PGPUB; IBM_TDB	2004/09/10 14:31
-	614	nitride and (((ion with implantation) and (((438/424,433,435,437).CCLS.) and @ad<20020724 not samsung.as.)) ((((((low near (energy dose)) and (ion with implantation)) and ("trench isolation" (sti "shallow trench isolation"))) and well) and @ad<20020724 not samsung.as.) and (438/$3 257/$3).ccls.))	USPAT; US-PGPUB; IBM_TDB	2004/09/10 13:59
-	116	(nitride and (((ion with implantation) and (((438/424,433,435,437).CCLS.) and @ad<20020724 not samsung.as.)) ((((((low near (energy dose)) and (ion with implantation)) and ("trench isolation" (sti "shallow trench isolation"))) and well) and @ad<20020724 not samsung.as.) and (438/$3 257/$3).ccls.))) and liner	USPAT; US-PGPUB; IBM_TDB	2004/09/10 14:30
-	7406	(dual two multipled) with implantation	USPAT; US-PGPUB; IBM_TDB	2004/09/10 14:31

-	613	((dual two multipled) with implantation) and ("trench isolation" (sti "shallow trench isolation"))	USPAT; US-PGPUB; IBM_TDB	2004/09/10 14:31
-	95472	CMOS PMOS NMOS	USPAT; US-PGPUB; IBM_TDB	2004/09/10 14:31
-	387	(CMOS PMOS NMOS) and (((dual two multipled) with implantation) and ("trench isolation" (sti "shallow trench isolation")))	USPAT; US-PGPUB; IBM_TDB	2004/09/10 14:31
-	296	((CMOS PMOS NMOS) and (((dual two multipled) with implantation) and ("trench isolation" (sti "shallow trench isolation")))) and @ad<20020724 not samsung.as.	USPAT; US-PGPUB; IBM_TDB	2004/09/10 14:31
-	227	nitride and (((CMOS PMOS NMOS) and (((dual two multipled) with implantation) and ("trench isolation" (sti "shallow trench isolation")))) and @ad<20020724 not samsung.as.)	USPAT; US-PGPUB; IBM_TDB	2004/09/10 14:54
-	217	(438/433).CCLS.	USPAT; US-PGPUB; IBM_TDB	2004/09/10 14:54
-	198	((438/433).CCLS.) and @ad<20020724 not samsung.as.	USPAT; US-PGPUB; IBM_TDB	2004/09/10 14:55
-	54	(("3617827") or ("3730786") or ("3885999") or ("3930909") or ("4339767") or ("4381953") or ("4412376") or ("4485552") or ("4553318") or ("4577397") or ("4641419") or ("4466178") or ("4653177") or ("4808543") or ("5015594") or ("5137837") or ("5260226") or ("5436174") or ("5627097") or ("5643822") or ("5759881") or ("5759885") or ("5780353") or ("5789288") or ("5795801") or ("5827763") or ("5874346") or ("5937287") or ("5963801") or ("5770504") or ("5861330") or ("6033949") or ("6054344") or ("6069057") or ("6177333") or ("6228726") or ("6248645") or ("6313011") or ("6342429") or ("6472301") or ("4900689") or ("4910160") or ("4997775") or ("5051805") or ("5055418") or ("5151378") or ("5206182") or ("5270224") or ("5409845") or ("5444285") or ("5447884") or ("5518937") or ("6649477") or ("6521493")).PN.	USPAT; US-PGPUB; IBM_TDB	2004/09/13 10:32
-	93	channeling with tail	USPAT; US-PGPUB; IBM_TDB	2004/09/13 10:33
-	16689	channel with stop	USPAT; US-PGPUB; IBM_TDB	2004/09/13 10:33
-	16778	channeling with tail) (channel with stop	USPAT; US-PGPUB; IBM_TDB	2004/09/13 10:33
-	71	(channeling with tail) and (438/$3 257/$3).ccls.	USPAT; US-PGPUB; IBM_TDB	2004/09/13 10:39

-	66	((channeling with tail) and (438/$3 257/$3).ccls.) and @ad<20020724 not samsung.as.	USPAT; US-PGPUB; IBM_TDB	2004/09/13 10:40
-	3350	(channel with stop) and (438/$3 257/$3).ccls.	USPAT; US-PGPUB; IBM_TDB	2004/09/13 10:39·
-	3007	((channel with stop) and (438/$3 257/$3).ccls.) and @ad<20020724 not samsung.as.	USPAT; US-PGPUB; IBM_TDB	2004/09/13 10:40
-	275	(((channel with stop) and (438/$3 257/$3).ccls.) and @ad<20020724 not samsung.as.) and (STI "shallow trench isolation")	USPAT; US-PGPUB; IBM_TDB	2004/09/13 10:40

(FILE 'HOME' ENTERED AT 13:22:31 ON 13 SEP 2004)

FILE 'INSPEC, CAPLUS' ENTERED AT 13:22:38 ON 13 SEP 2004
L1   464 S CHANNEL STOP
L2   4114 S STI
L3   2607 S SHALLOW TRENCH ISOLATION
L4   16 S (L2 OR L3) AND L1
L5   49 S WELL RESISTANCE
L6   4 S L5 AND (L2 OR L3)